

## **GA080TH65**

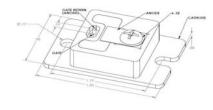
### Silicon Carbide Thyristor

V <sub>FBM</sub>	=	6500 V	
I <sub>T(AVM)</sub>	=	80 A	
Q <sub>rr</sub>	=	4.2 μC	

#### **Features**

- 6500 V Asymmetric SiC NPNP Thyristor
- 150 °C operating temperature
- Robust compact fully soldered package
- SOT-227 (ISOTOP) base plate form factor
- Fast turn on characteristics
- Lowest in class Q<sub>rr</sub>/I<sub>T(AVM)</sub>

- Applications
   Grid Tied Solar Inverters
- Wind Power Inverters
- HVDC Power Conversion
- Utility Scale Power Conversion
- Trigger Circuits/Ignition Circuits



**Package** 



#### **Maximum Ratings**

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak forward voltage	$V_{\scriptscriptstyle{FBM}}$	T <sub>j</sub> = 25 °C	6500	V
Repetitive peak reverse voltage	$V_{RBM}$	T <sub>j</sub> = 25 °C	50	V
Maximum average on-state current	I <sub>T(AVM)</sub>	T <sub>c</sub> ≤ 125 °C	80	Α
RMS on-state current	I <sub>T(RMS)</sub>	T <sub>c</sub> ≤ 125 °C	139	Α
Non-repetitive peak on-state current	I <sub>T.max</sub>	$T_{c}$ = 25 °C, $t_{p}$ = 2 us, D = 0.1	tbd	Α
Power dissipation	P <sub>tot</sub>	T <sub>C</sub> = 25 °C	1563	W
Operating and storage temperature	T <sub>i</sub> , T <sub>sto</sub>		-55 to 150	°C

#### **Electrical Characteristics**

Parameter	Cumbal	Conditions	Values		Unit	
	Symbol		min.	typ.	max.	Oill
Maximum pook on atata valtaga	V	I <sub>K</sub> = -80 A, T <sub>j</sub> = 25 °C		-3.70		W
Maximum peak on state voltage	$V_{KA(ON)}$	$I_{\kappa} = -80 \text{ A}, T_{j} = 150 ^{\circ}\text{C}$		-3.45		V
Anode-cathode threshold voltage	$V_{KA(TO)}$	T <sub>j</sub> = 25 °C (150 °C)		-3.0(-2.7)		V
Anode-cathode slope resistance	R <sub>AK</sub>	$T_{j}$ = 25 °C (150 °C), $I_{K}$ = -80 A		6.0(6.3)		mΩ
Lookaga current	1	$V_{KA} = -6500 \text{ V}, V_{GA} = 0 \text{ V}, T_{j} = 25 ^{\circ}\text{C}$		15		μA
Leakage current	'L	$V_{KA} = -6500 \text{ V}, V_{GA} = 0 \text{ V}, T_{j} = 150 ^{\circ}\text{C}$		50		
Gate trigger current	I <sub>GT</sub>	$T_{j}$ = 25 °C, $t_{p}$ = 10 $\mu$ s		-100		mA
Holding current	I <sub>H</sub>	T <sub>j</sub> = 25 °C		tbd		mA
Rise time	t <sub>R</sub>	I <sub>G</sub> = -3 A, V <sub>KA</sub> = -2200 V		190		ns
Delay time	$t_{_{\mathrm{D}}}$	$I_{K} = -80 \text{ A}, T_{j} = 25 ^{\circ}\text{C}$		50		ns
Reverse recovery charge	$Q_{_{\mathrm{ff}}}$			4.2		μC
Recovered charge, 50% chord	$Q_{ra}$	$dI/dt = 430 \text{ A/us}, I_{K} = -70 \text{ A}, V_{KA} = 20 \text{ V}$		2.3		μC
Reverse recovery current	I <sub>m</sub>	$dV/dt(re-app) = -460 V/us, T_j = 25 °C$		20		Α
Circuit commutated turn-off time	t <sub>q</sub>	,		10.1		μs

#### **Thermal Characteristics**

Thermal resistance, junction - case	R <sub>thJC</sub>		0.08	°C/W
Mechanical Properties				
Mounting torque for base	M <sub>b</sub>	Heat sink surface must be optically flat	1.5	Nm
Mounting torque for top	$M_{t}$		1.3	Nm

W,

1. Considering worst case  $Z_{th}$  conditions

0000

30

Weight



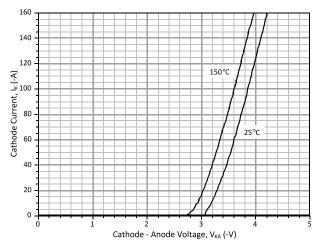


Figure 1: Typical On State Characteristics

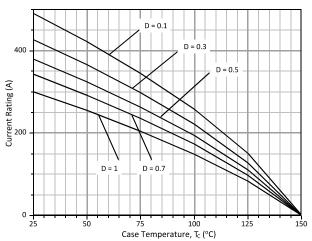


Figure 3: Typical Current Derating Curves (D =  $t_p/T$ ,  $t_p$  = 400  $\mu s^1$ )

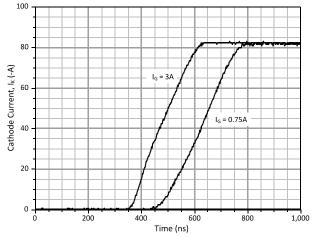


Figure 5: Typical Turn On Characteristics at 25 °C

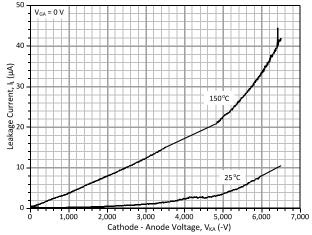


Figure 2: Typical Forward Blocking Characteristics

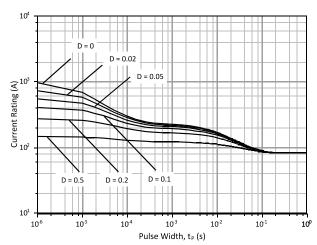


Figure 4: Typical Current Rating versus Pulse Duration Curves at T  $_{\rm C}$  = 120  $^{\rm o}{\rm C}$ 

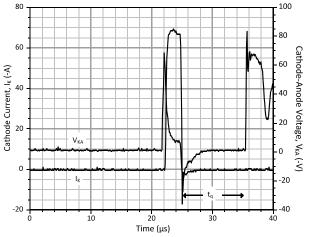
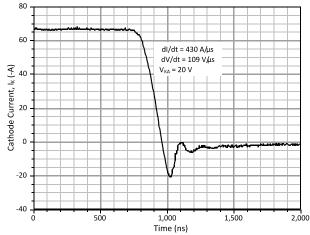


Figure 6: Typical Turn Off Characteristics at 25 °C







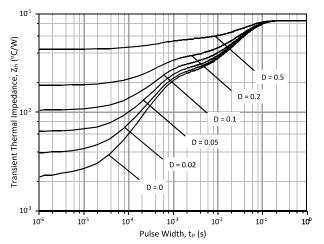


Figure 8: Typical Transient Thermal Impedance

Revision History				
Date	Revision	Comments	Supersedes	
2010/11/13	1	First generation release		

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